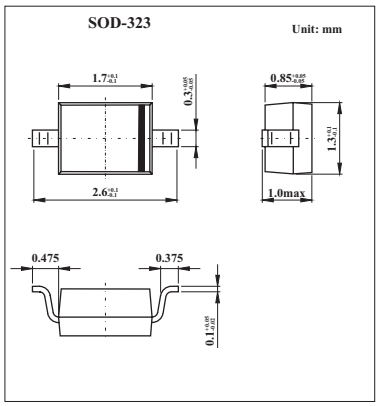
Silicon Epitaxial Planar Diode

ZDV214



■ Features

- High Capacitance Ratio : C2V/C25V=6.5(Typ.)
- Low Series Resistance : rS=0.4 Ω (Typ.)
- Excellent C-V Characteristics, and Small Tracking Error.
- Useful for Small Size Tuner.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	32	V
Peak Reverse Voltage	V_{RM}	35 (R_L=10K Ω)	V
Junction Temperature	T_j	125	℃
Storage Temperature Range	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	I_R = 1 μ A	30			V
Reverse Current	I_R	V_R = 28 V			10	nA
Capacitance	C_{2V}	f = 1 MHz;V_R = 2 V	14.16		16.25	pF
	C_{25V}	f = 1 MHz;V_R = 25 V	2.11		2.43	
Capacitance Ratio	C_{2V}/C_{25V}		5.9	6.5	7.15	
Series Resistance	r_s	V_R = 5V, f = 470 MHz		0.4	0.55	Ω

Note :

Available in matched group for capacitance to 2.5%.

$$\frac{C(Max.)-C(Min.)}{C(Min.)} \leqslant 0.025$$

■ Marking

Marking	UO